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Title: DUAL-DAMASCENE DIELECTRIC STRUCTURES AND METHODS FOR MAKING THE SAME

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TITLE: Fluoropolymer interlayer dielectric by chemical vapor deposition

----- KWIC -----

[0018] Thin film devices on which fluoropolymer layers may be formed by the present process comprise devices known in the microelectronics industry as semiconductor wafers, integrated circuits, flat panel displays, micromechanical devices, microelectrical mechanical systems, and thin film optical and optoelectrical devices. The surface of such thin film devices on which a fluoropolymer layer may be formed by the present process include: silicon; silicon dioxide; silicon nitride; silicon oxynitride; silicon carbide; "~~carbon doped~~" oxides (e.g. spin-on materials such as ~~HSQ~~ and ~~MSQ~~, as well as CVD materials such as ~~Coral TM~~ and ~~Black Diamond TM~~); phosphosilicate, borosilicate and borophosphosilicate glass; polyimides; aluminum; copper; tungsten; molybdenum; titanium; tantalum; suicides and nitrides of aluminum, copper, tungsten, molybdenum, titanium and tantalum; and conductive alloys of aluminum, copper, tungsten, molybdenum, titanium, and tantalum, including aluminum doped with copper and/or silicon.

HSQ = Carbon doped
oxide